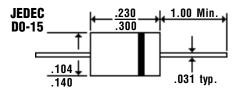


# Preliminary Data Sheet | 2.0 Amp Glass Passivated Sintered Ultra - Fast Rectifiers

Semiconductor Description

# **UGPZ20A... 20G Series**

# **Mechanical Dimensions**



## Features

- LOWEST COST FOR GLASS SINTERED ULTRA FAST CONSTRUCTION
- LOWEST V\_ FOR GLASS SINTERED **ULTRA - FAST CONSTRUCTION**
- TYPICAL I<sub>R</sub> < 100 nAmps

- 2.0 AMP OPERATION @ T<sub>A</sub> = 55°C, WITH **NO THERMAL RUNAWAY**
- SINTERED GLASS CAVITY-FREE JUNCTION

Electrical Characteristics @ 25°C.	UGPZ20A 20G Series				Units
Maximum Ratings	20A	20B	20D	20G	
Peak Repetitive Reverse VoltageV <sub>RRM</sub>	50	100	200	400	Volts
RMS Reverse VoltageV <sub>R(rms)</sub>	35	70	140	280	Volts
DC Blocking VoltageV <sub>DC</sub>	50	100	200	400	Volts
Average Forward Rectified CurrentI $_{F(av)}$ Current 3/8" Lead Length @ $T_A = 55^{\circ}C$	2.0			Amps	
Non-Repetitive Peak Forward Surge CurrentI <sub>FSM</sub> 8.3mS, ½ Sine Wave Superimposed on Rated Load	80			Amps	
Forward Voltage @ Rated Forward Current and 25°CV <sub>F</sub>	<	0.95	>	1.25	Volts
Full Load Reverse CurrentI <sub>R</sub> (av) Full Cycle Average @ T <sub>A</sub> = 55°C		1	00		μAmp
DC Reverse Current $I_{R(max)}$ @ Rated DC Blocking Voltage $T_A = 25^{\circ}\text{C}$ $T_A = 150^{\circ}\text{C}$			00		μAmp: μAmp:
Typical Junction CapacitanceC <sub>J</sub> (Note 1)		3	35		pF
Maximum Thermal ResistanceR <sub>eJA</sub> (Note 2)		2	22		°C/W
Maximum Reverse Recovery Timet <sub>RR</sub> (Note 3)		3	35		nS
Operating & Storage Temperature RangeT <sub>.</sub> , T <sub>STRG</sub>		65 t	to 175		°C

NOTES: 1. Measured @ 1 MHZ and applied reverse voltage of 4.0V.

- 2. Thermal Resistance from Junction to Ambient at 3/8" Lead Length, P.C. Board Mounted.
- 3. Reverse Recovery Condition  $I_F = 0.5A$ ,  $I_R = 1.0A$ ,  $I_{RR} = 0.25A$ .